

Title (en)

SEMICONDUCTOR COMPONENT AND METHOD FOR PRODUCING IT AND USE FOR IT

Title (de)

HALBLEITERBAUELEMENT UND VERFAHREN ZU DESSEN HERSTELLUNG SOWIE DESSEN VERWENDUNG

Title (fr)

COMPOSANT SEMI-CONDUCTEUR: PROCÉDÉ DE FABRICATION ET UTILISATION

Publication

EP 1987548 A1 20081105 (DE)

Application

EP 07711548 A 20070215

Priority

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- DE 102006007797 A 20060220

Abstract (en)

[origin: WO2007096084A1] The invention relates to a method for producing a semiconductor component with at least one surface made optically reflective, in which a silicon wafer, which has an etchable dielectric layer at least in certain regions on at least one of its surfaces, is provided with a silicon-containing masking layer for shielding it from fluidic media. A layer of aluminium is additionally deposited on the masking layer and a thermal treatment of the semiconductor component is subsequently performed, causing the silicon in the aluminium to break down. The invention also relates to a corresponding semiconductor component made from a silicon wafer with at least one surface made optically reflective. Semiconductor components of this type are used in particular as solar cells.

IPC 8 full level

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CPC (source: EP KR US)

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